

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Takuji MATSUMOTO, et al.

SERIAL NO: 10/754,539

FILED: January 12, 2004

FOR: SEMICONDUCTOR DEVICE



GAU:

EXAMINER:

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.

A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.

A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.

No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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DOCKET NO.: 247561US2/hc



Page 1 of 1

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**STATEMENT OF RELEVANCY**

**Reference AO (JP 10-209167) on "Form PTO 1449" is discussed in the specification.**



Form PTO 1449 (Modified) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF REFERENCES CITED BY APPLICANT		ATTY DOCKET NO. 247561US2		SERIAL NO. 10/754,539	
		APPLICANT Takuji MATSUMOTO, et al.			
		FILING DATE January 12, 2004		GROUP	
		<b>U.S. PATENT DOCUMENTS</b>			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS SUB CLASS
AA					
AB					
AC					
AD					
AE					
AF					
AG					
AH					
AI					
AJ					
AK					
AL					
AM					
AN					
<b>FOREIGN PATENT DOCUMENTS</b>					
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
AO	10-209167	08/07/1998	JAPAN (with English extract)		
AP					
AQ					
AR					
AS					
AT					
AU					
AV					
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>					
AW	Y. HIRANO, et al., IEEE International SOI Conference, pages 131-132, "BULK-LAYOUT-COMPATIBLE 0.18 $\mu$ m SOI-CMOS TECHNOLOGY USING BODY-FIXED PARTIAL TRENCH ISOLATION (PTI)", October 1999				
AX	S. MAEDA, et al., Symposium on VLSI Technology Digest of Technical Papers, pages 154-155, "IMPACT OF 0.18 $\mu$ m SOI CMOS TECHNOLOGY USING HYBRID TRENCH ISOLATION WITH HIGH RESISTIVITY SUBSTRATE ON EMBEDDED RF/ANALOG APPLICATIONS", 2000				
AY	Y. HIRANO, et al., IEEE, IEDM, pages 467-470, "IMPACT OF 0.10 $\mu$ m SOI CMOS WITH BODY-TIED HYBRID TRENCH ISOLATION STRUCTURE TO BREAK THROUGH THE SCALING CRISIS OF SILICON TECHNOLOGY", 2000				
AZ	S. MAEDA, et al., Extended Abstracts of the 2001 International Conference on Solid State Devices and Materials, pages 270-271, "A HIGHLY RELIABLE 0.18 $\mu$ m SOI CMOS TECHNOLOGY FOR 3.3V/1.8V OPERATION USING HYBRID TRENCH ISOLATION AND DUAL GATE OXIDE", 2001				<input type="checkbox"/> Additional References sheet(s) attached
Examiner					Date Considered
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

**LIST OF RELATED CASES**

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/Applicant</u>
0057-2567-2YY	09/466,934	12/20/99	YAMAGUCHI et al.
221848US2 CONT	10/120,485	04/12/02	YAMAGUCHI et al.
224869US2	10/192,657	07/11/02	MATSUMOTO et al.
226776US2	10/216,363	08/12/02	MATSUMOTO et al.
226976US2	10/237,022	09/09/02	IWAMATSU et al.
247561US2*	10/754,539	01/12/04	MATSUMOTO et al.

\*Present Application; listed for information  
GJM/akh